PE7150M

P-Channel Enhancement Mode Power MOSFET

Description

The PE7150M uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

General Features

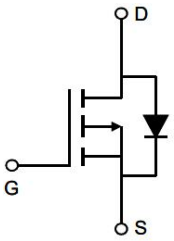
- V_{DS} = -18V, I_D = -50A

  $R_{DS(ON)}$ < 6.3mΩ @ V_{GS}=-4.5V
  $R_{DS(ON)}$ < 7.0mΩ @ V_{GS}=-3.8V
  $R_{DS(ON)}$ < 8.1mΩ @ V_{GS}=-3.1V
  $R_{DS(ON)}$ < 9.0mΩ @ V_{GS}=-2.5V

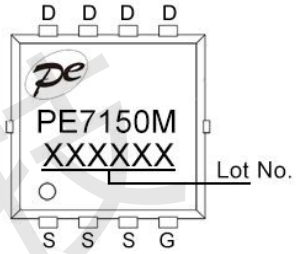
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package
- Good stability and uniformity with high E_{AS}

Application

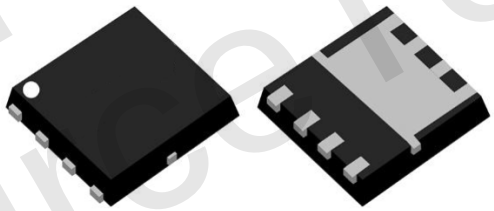
- PWM applications
- Load switch
- Power management
- Battery protection



Schematic diagram



Marking and pin assignment



PDFN3.3x3.3-8L

Absolute Maximum Ratings (TC=25℃ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-18	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous (TC=25℃)	I_D	-50	A
Pulsed Drain Current (Note 1)	I_{DM}	-150	A
Maximum Power Dissipation	P_D	30	W
Avalanche Current	I_{AS}	43	A
Avalanche Energy (L=0.1mH)	E_{AS}	92	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.2	℃/W

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Electrical Characteristics (TC=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=-250μA	-18	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-12V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.45	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V,I_D=-15A	-	5	6.3	mΩ
		V_{GS}=-3.8V,I_D=-12A	-	5.3	7.0	mΩ
		V_{GS}=-3.1V,I_D=-10A	-	5.8	8.1	mΩ
		V_{GS}=-2.5V,I_D=-10A	-	6.5	9.0	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-10A	-	95	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V, F=1.0MHz	-	4210	-	pF
Output Capacitance	C_{oss}		-	650	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	380	-	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V,R_L=1Ω, V_{GS}=-10V,R_G=3Ω	-	18	-	nS
Turn-on Rise Time	t_r		-	32	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	126	-	nS
Turn-Off Fall Time	t_f		-	59	-	nS
Total Gate Charge	Q_g	V_{DS}=-10V,I_D=-14A, V_{GS}=-4.5V	-	44	-	nC
Gate-Source Charge	Q_{gs}		-	9	-	nC
Gate-Drain Charge	Q_{gd}		-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-17	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to product.

Typical Electrical and Thermal Characteristics

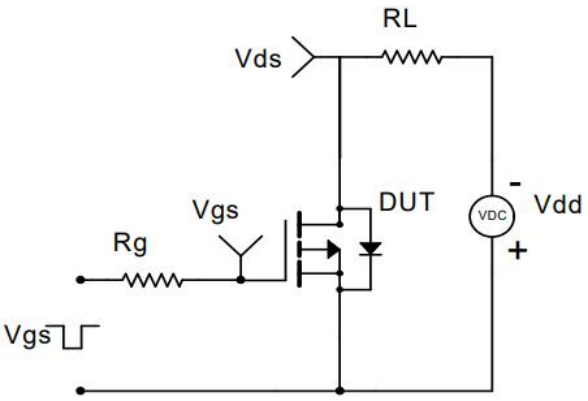


Figure 1 Switching Test Circuit

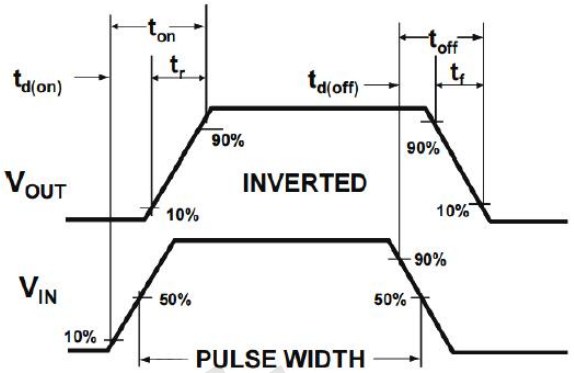


Figure 2 Switching Waveform

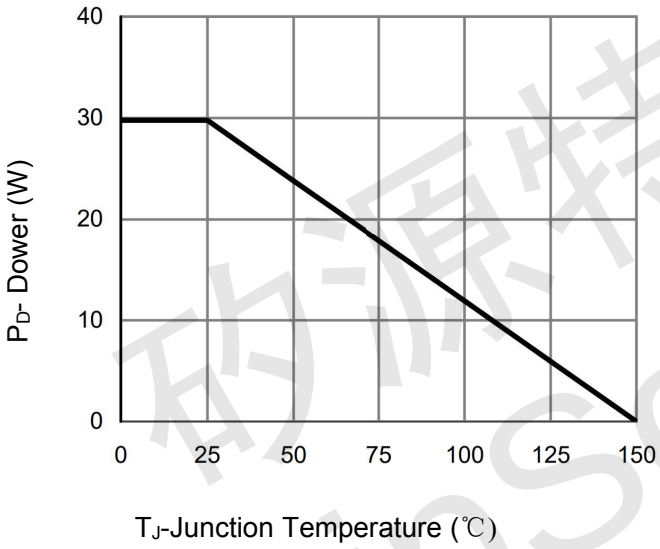


Figure 3 Power De-rating

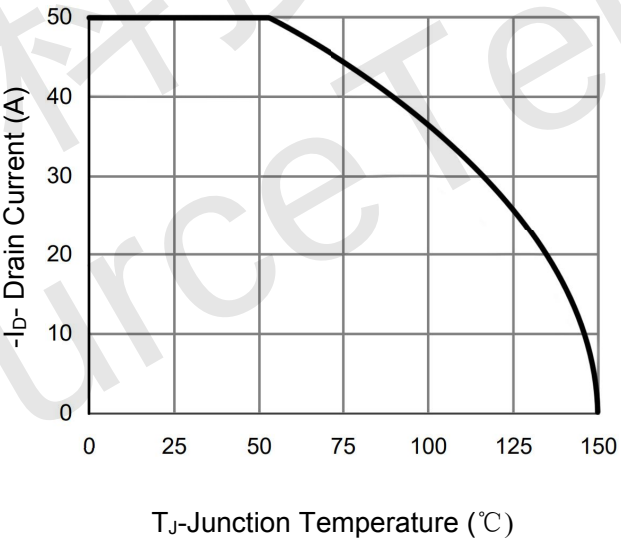


Figure 4 Drain Current

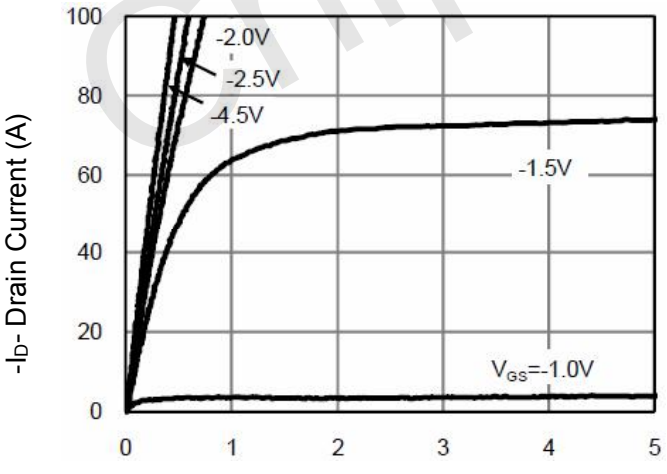


Figure 5 Output Characteristics

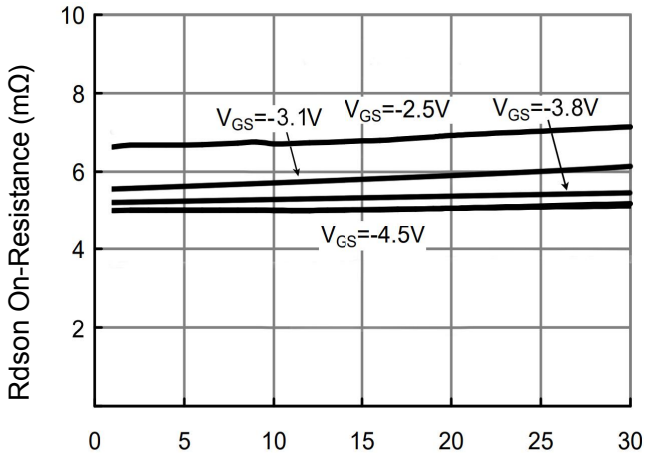


Figure 6 Rdson vs Drain Current

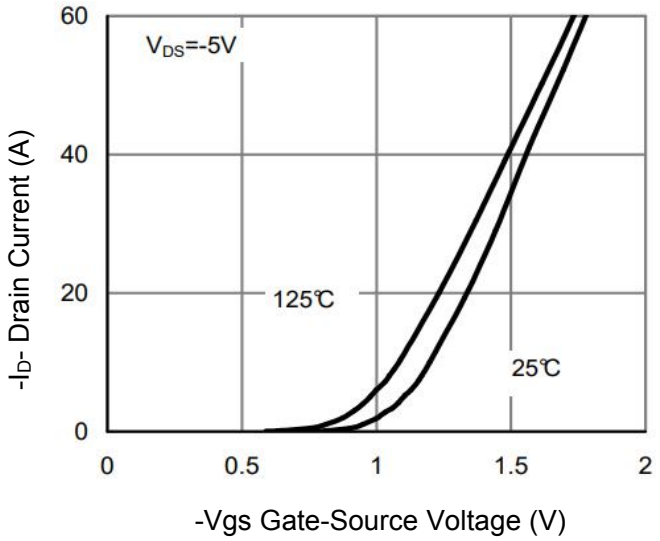


Figure 7 Transfer Characteristics

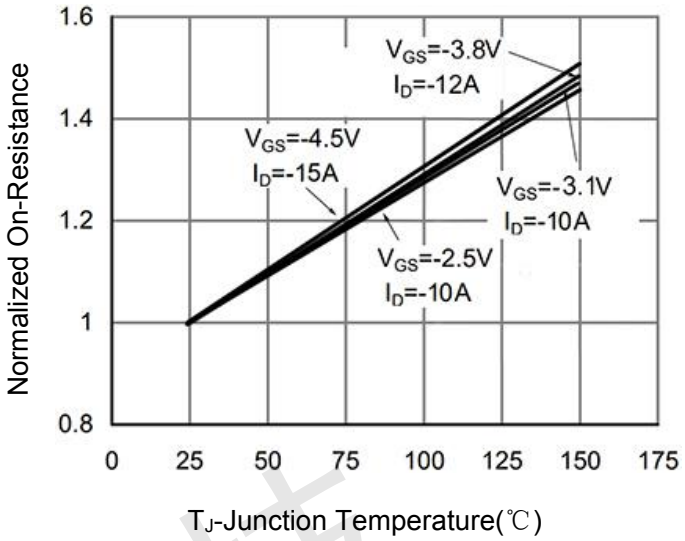


Figure 8 Rdson vs Junction Temperature

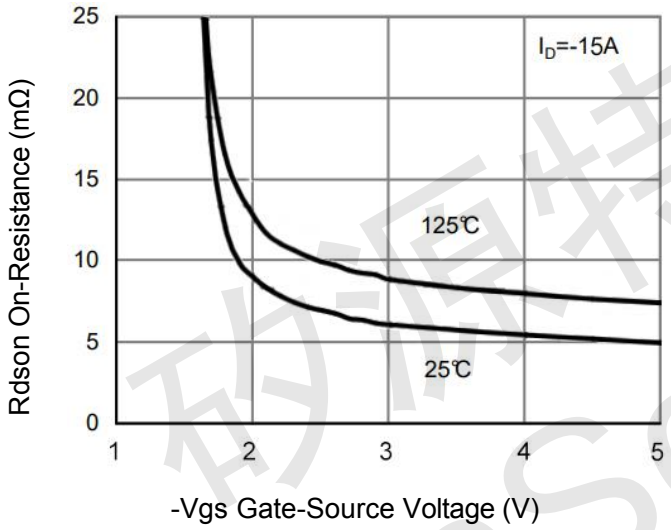


Figure 9 Rdson vs Vgs

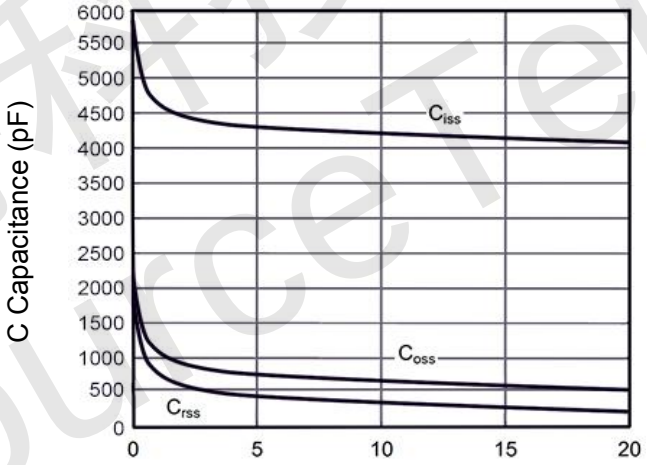


Figure 10 Capacitance vs Vds

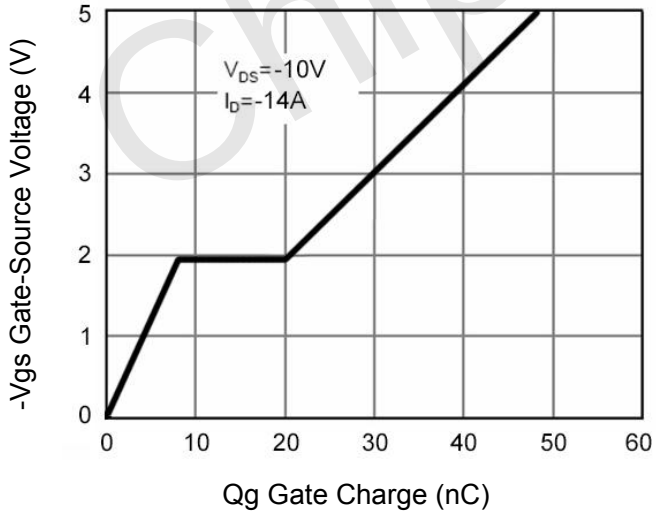


Figure 11 Gate Charge

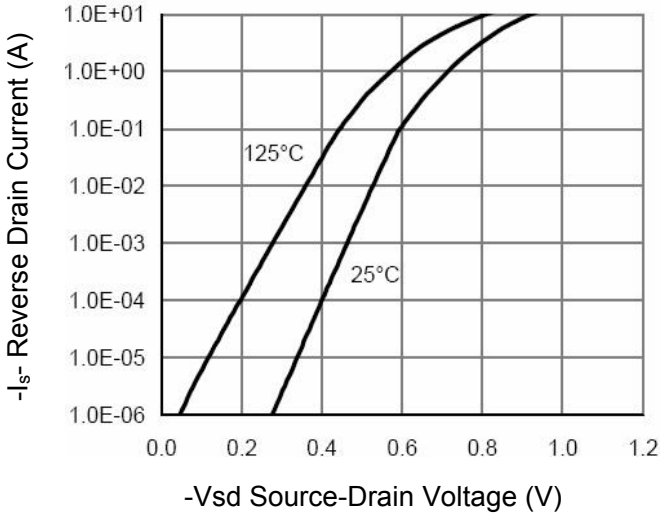


Figure 12 Source- Drain Diode Forward

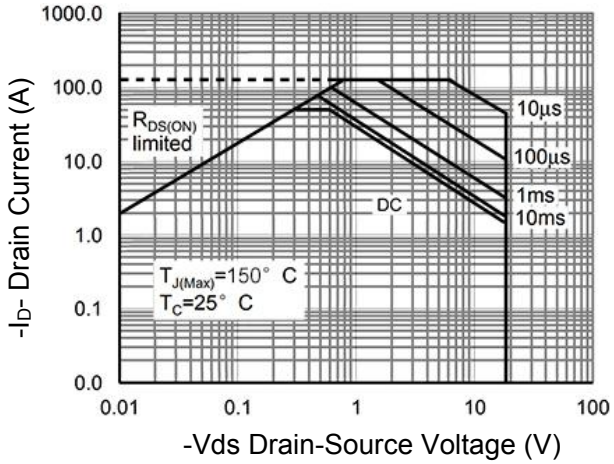


Figure 13 Safe Operation Area

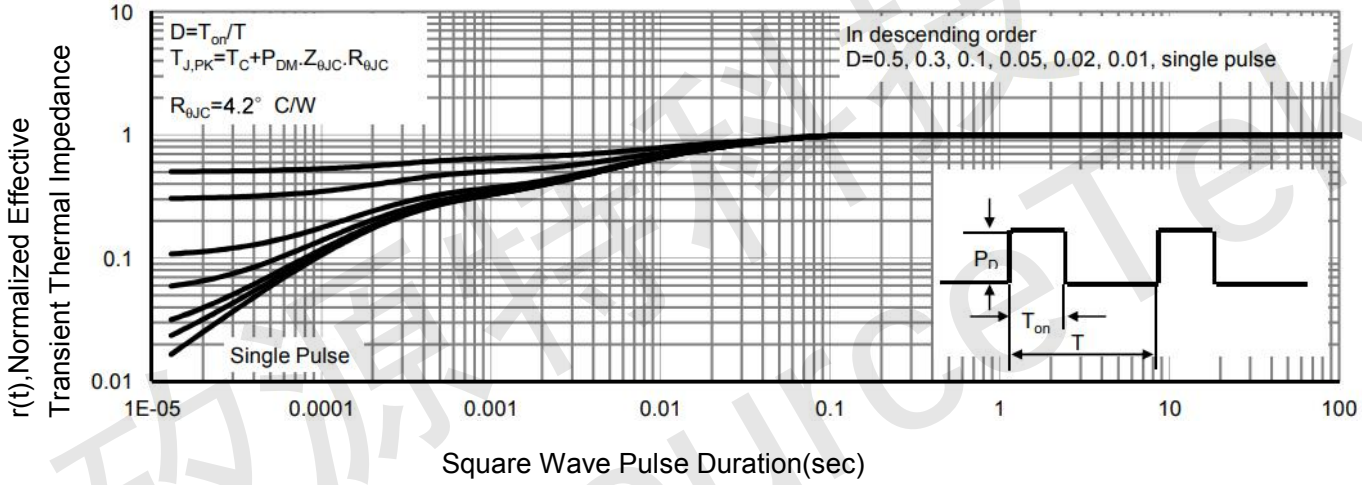
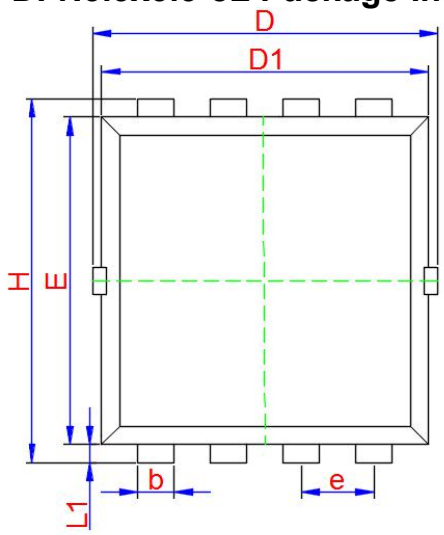
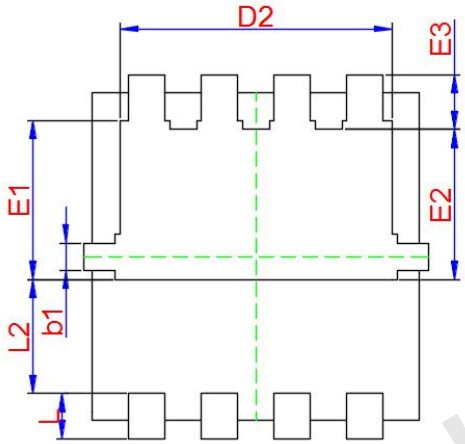
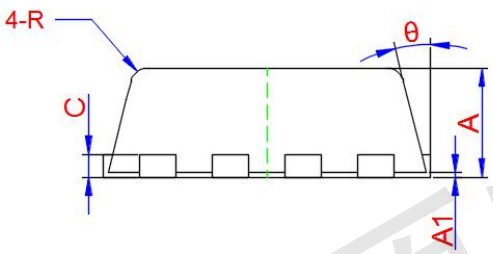


Figure 14 Normalized Maximum Transient Thermal Impedance

PDFN3.3x3.3-8L Package Information







Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.700	0.800	0.900
A1	0.000	0.030	0.050
b	0.240	0.300	0.350
b1	0.080	0.130	0.180
c	0.152 TYP.		
D	3.250	3.320	3.400
D1	3.050	3.150	3.250
D2	2.400	2.500	2.600
E	3.000	3.100	3.200
E1	1.350	1.450	1.550
E2	1.200	1.300	1.400
E3	0.400	0.500	0.600
e	0.650 TYP.		
H	3.200	3.300	3.400
L	0.300	0.400	0.500
L1	0.100	0.150	0.200
L2	1.130 TYP.		
R	0.200 TYP.		
θ	6°	10°	14°